

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

B.Tech I Year I Semester Supplementary Examinations February-2024

BASIC ELECTRONICS ENGINEERING

(Common to CSE,CSM, CAD,CAI,CCC,CSIT & CIC)

Time: 3 Hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Draw the atomic structure of a semiconductor and explain why an Intrinsic semiconductor is relatively a poor conductor of electricity. CO1 L4 6M
b Explain diffusion current with expressions. CO4 L2 6M

OR

- 2 a Describe the charge neutrality in semiconductors in detail. CO1 L2 6M
b Compare p-type and n-type semiconductors. CO1 L4 6M

UNIT-II

- 3 a Illustrate the action of PN junction diode under forward bias and reverse bias and sketch its V-I Characteristics. CO1 L2 6M
b Discuss about Breakdown mechanisms in PN Junction Diode. CO5 L2 6M

OR

- 4 a Analyze the current components in a PN diode and derive the expression for diode current. CO4 L4 6M
b Explain the Zener voltage regulator with a neat diagram. CO3 L2 6M

UNIT-III

- 5 a Derive the expressions for Average DC current, Average DC Voltage, RMS Value of Current, DC Power Output, AC Power input and Efficiency of a Half Wave Rectifier. CO2 L4 6M
b A voltage of $200\cos\omega t$ is applied to Half Wave Rectifier with load resistance of 5 kohm, find the maximum dc current, rms current and ripple factor. CO2 L3 6M

OR

- 6 a Demonstrate the working principle of LC filter with neat diagram and derive the expression for its ripple factor CO3 L2 8M
b Compare the Full wave and Half wave rectifiers. CO2 L4 4M

UNIT-IV

- 7 a Explain the current components of PNP transistor. CO4 L3 6M
b Draw the Input and Output characteristics of a BJT in CB Configuration. CO1 L4 6M

OR

- 8 a Define Transistor Biasing and explain the need for Biasing. CO2 L2 8M
b Discuss about Sensistor Compensation Technique. CO2 L2 4M

UNIT-V

- 9 a Explain the construction and working principle of N-channel JFET. CO1 L3 6M
b List the types of JFET Biasing and Explain Briefly the setting of Operating Point. CO1 L2 6M

OR

- 10 a Sketch the transfer and drain characteristics of E-only MOSFET. CO5 L3 6M
b Derive the Drain to Source resistance, Trans-conductance and amplification factor from Characteristics of JFET. CO4 L4 6M

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